

# DATA SHEET

## **PDTC124E series**

NPN resistor-equipped transistors;

$R1 = 22\text{ k}\Omega$ ,  $R2 = 22\text{ k}\Omega$

Product specification  
Supersedes data of 2002 Mar 14

2003 Apr 14

## NPN resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

## PDTC124E series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	50	V
I <sub>O</sub>	output current (DC)	–	100	mA
R1	bias resistor	22	–	k $\Omega$
R2	bias resistor	22	–	k $\Omega$

### DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	PNP COMPLEMENT
	PHILIPS	EIAJ		
PDTC124EE	SOT416	SC-75	06	PDTA124EE
PDTC124EEF	SOT490	SC-89	36	PDTA124EEF
PDTC124EK	SOT346	SC-59	06	PDTA124EK
PDTC124EM	SOT883	SC-101	DX	PDTA124EM
PDTC124ES	SOT54 (TO-92)	SC-43	TC124E	PDTA124ES
PDTC124ET	SOT23	–	*17 <sup>(1)</sup>	PDTA124ET
PDTC124EU	SOT323	SC-70	*06 <sup>(1)</sup>	PDTA124EU

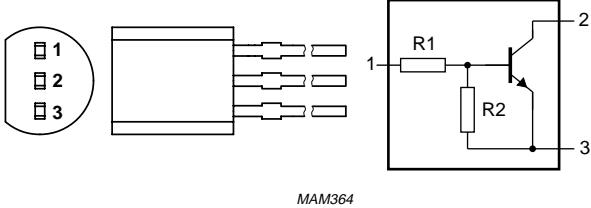
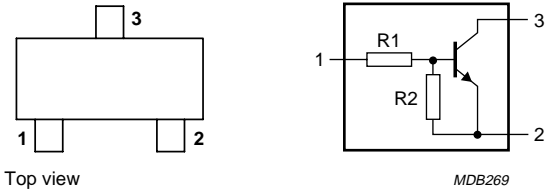
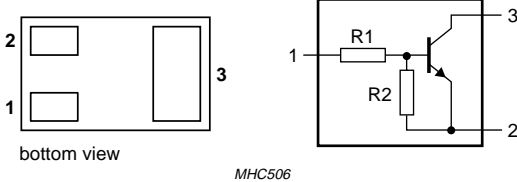
### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 22 kΩ

PDTC124E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC124ES	 MAM364	1 2 3	base collector emitter
PDTC124EE PDTC124EEF PDTC124EK PDTC124ET PDTC124EU	 Top view MDB269	1 2 3	base emitter collector
PDTC124EM	 bottom view MHC506	1 2 3	base emitter collector

# NPN resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

## PDTC124E series

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	10	V
V <sub>I</sub>	input voltage				
	positive		–	+40	V
	negative		–	–10	V
I <sub>O</sub>	output current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT416	note 1	–	150	mW
	SOT490	notes 1 and 2	–	250	mW
	SOT883	notes 2 and 3	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

NPN resistor-equipped transistors;  
R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

## PDTC124E series

**CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0	–	–	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	–	–	1	$\mu$ A
		V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0; T <sub>j</sub> = 150 °C	–	–	50	$\mu$ A
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	–	–	180	$\mu$ A
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA	60	–	–	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	–	–	150	mV
V <sub>i(off)</sub>	input-off voltage	I <sub>C</sub> = 100 $\mu$ A; V <sub>CE</sub> = 5 V	–	1.1	0.8	V
V <sub>i(on)</sub>	input-on voltage	I <sub>C</sub> = 5 mA; V <sub>CE</sub> = 0.3 V	2.5	1.7	–	V
R1	input resistor		15.4	22	28.6	k $\Omega$
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = I <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	–	–	2.5	pF

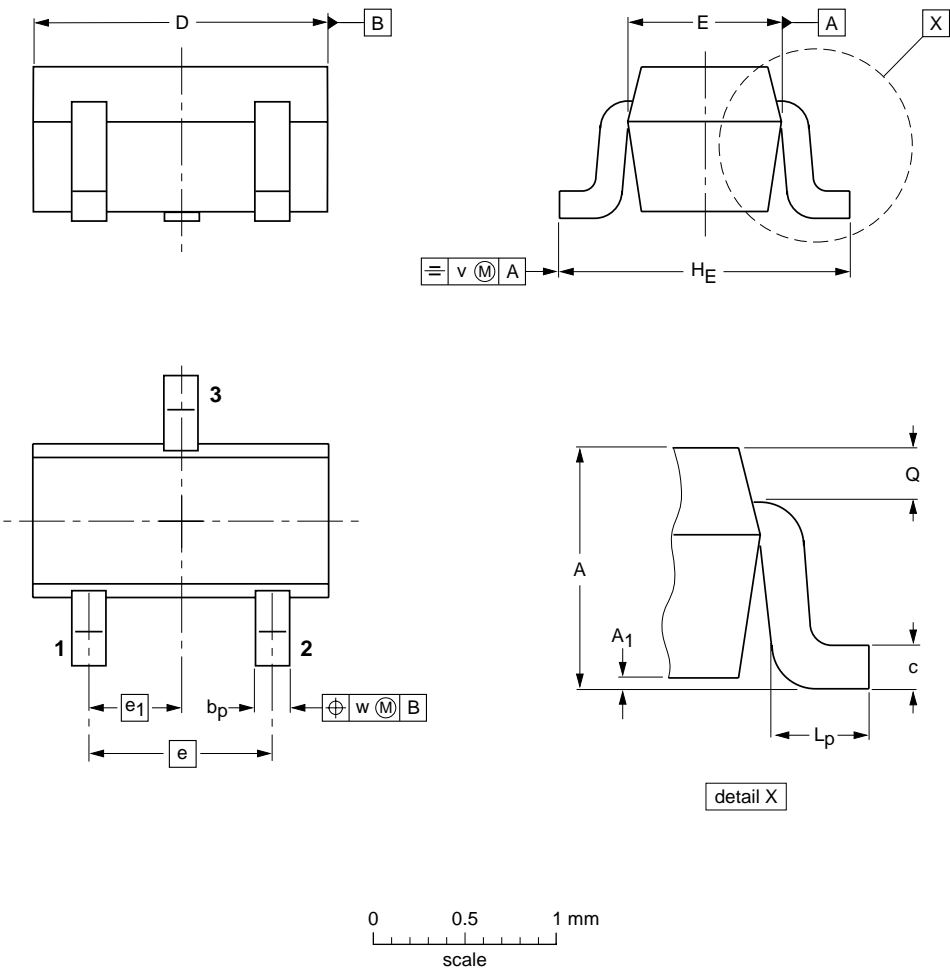
NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 22 kΩ

PDTC124E series

PACKAGE OUTLINES

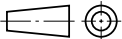
Plastic surface mounted package; 3 leads

SOT416



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

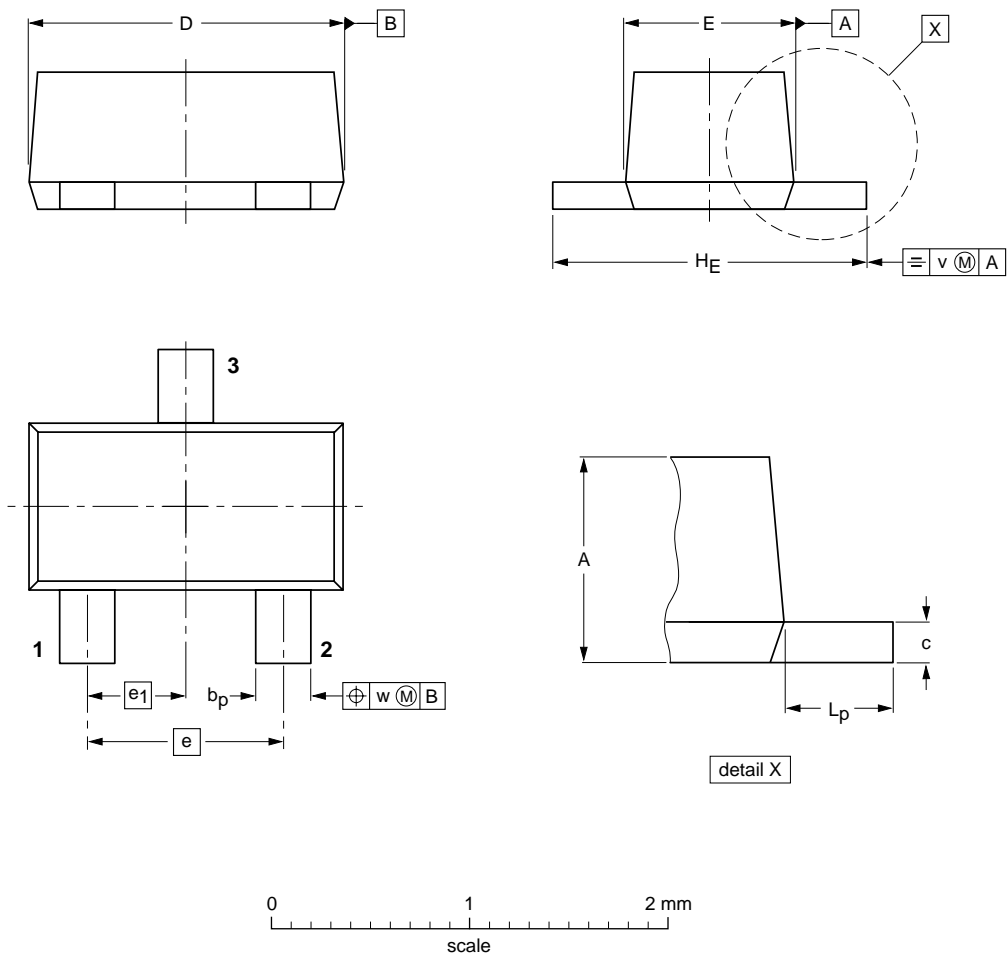
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT416			SC-75			97-02-28

NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 22 kΩ

PDTC124E series


Plastic surface mounted package; 3 leads

SOT490



DIMENSIONS (mm are the original dimensions)

UNIT	A	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

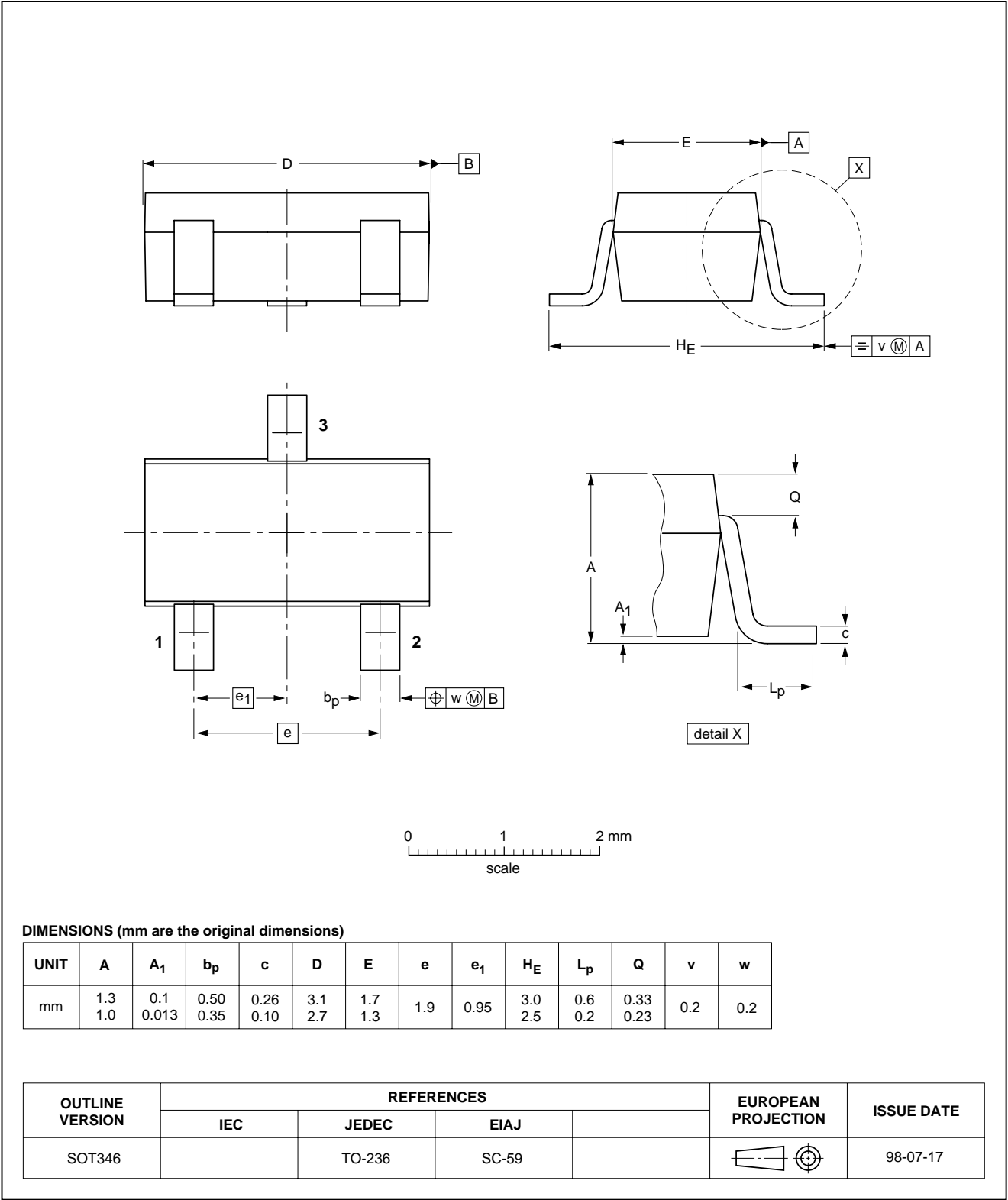
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT490			SC-89			98-10-23

NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 22 kΩ

PDTC124E series

Plastic surface mounted package; 3 leads

SOT346



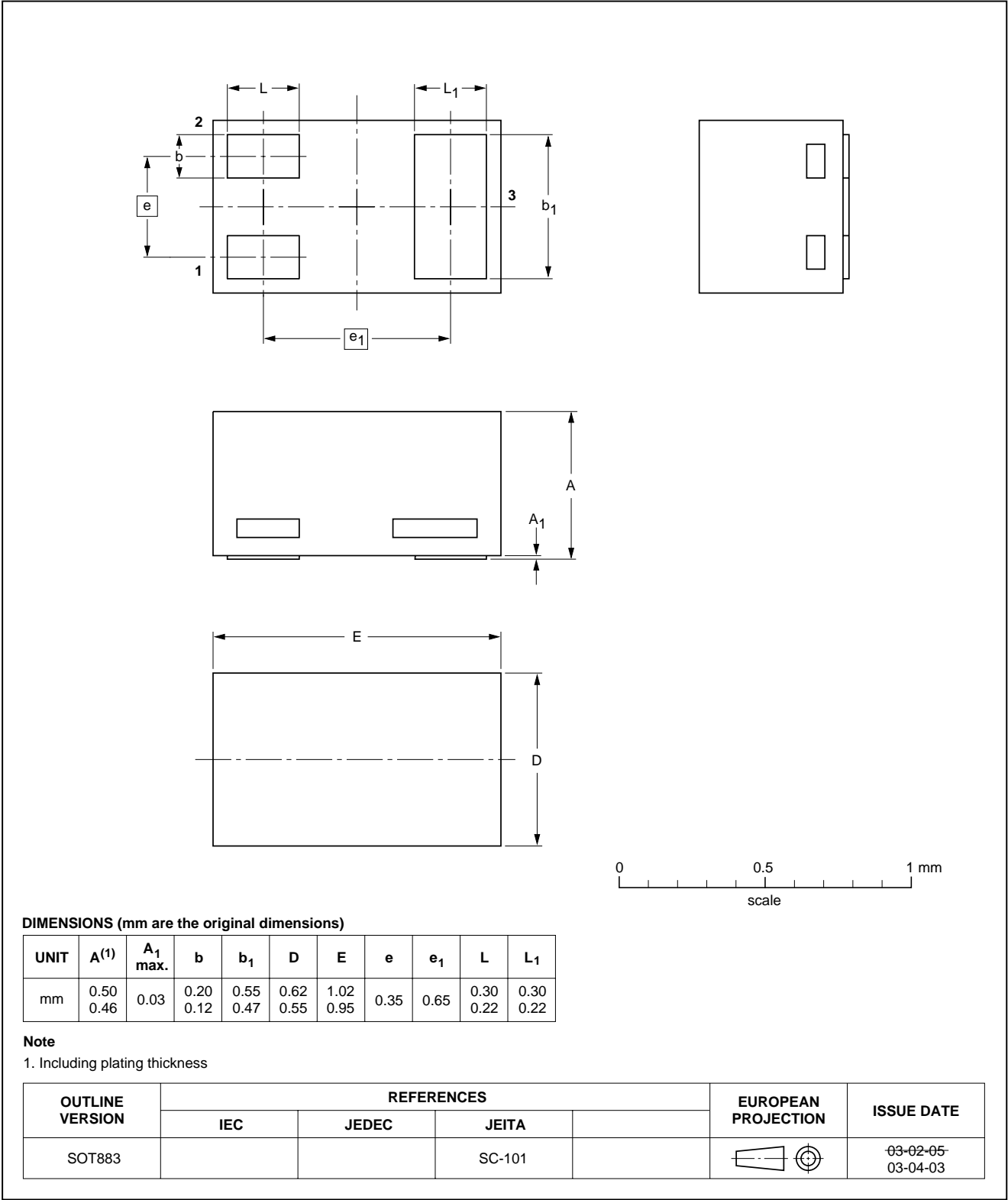


NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 22 kΩ

PDTC124E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

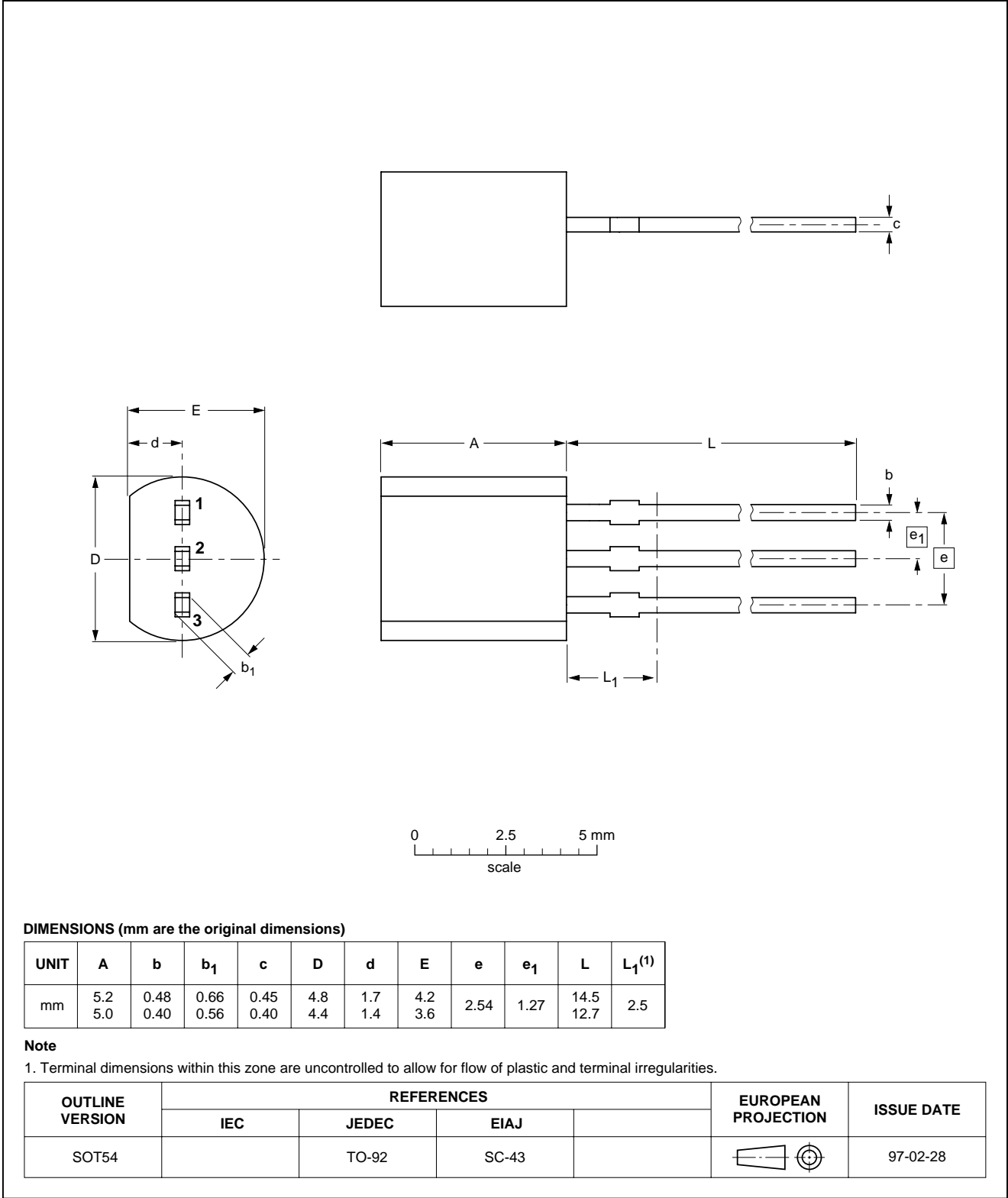


NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 22 kΩ

PDTC124E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

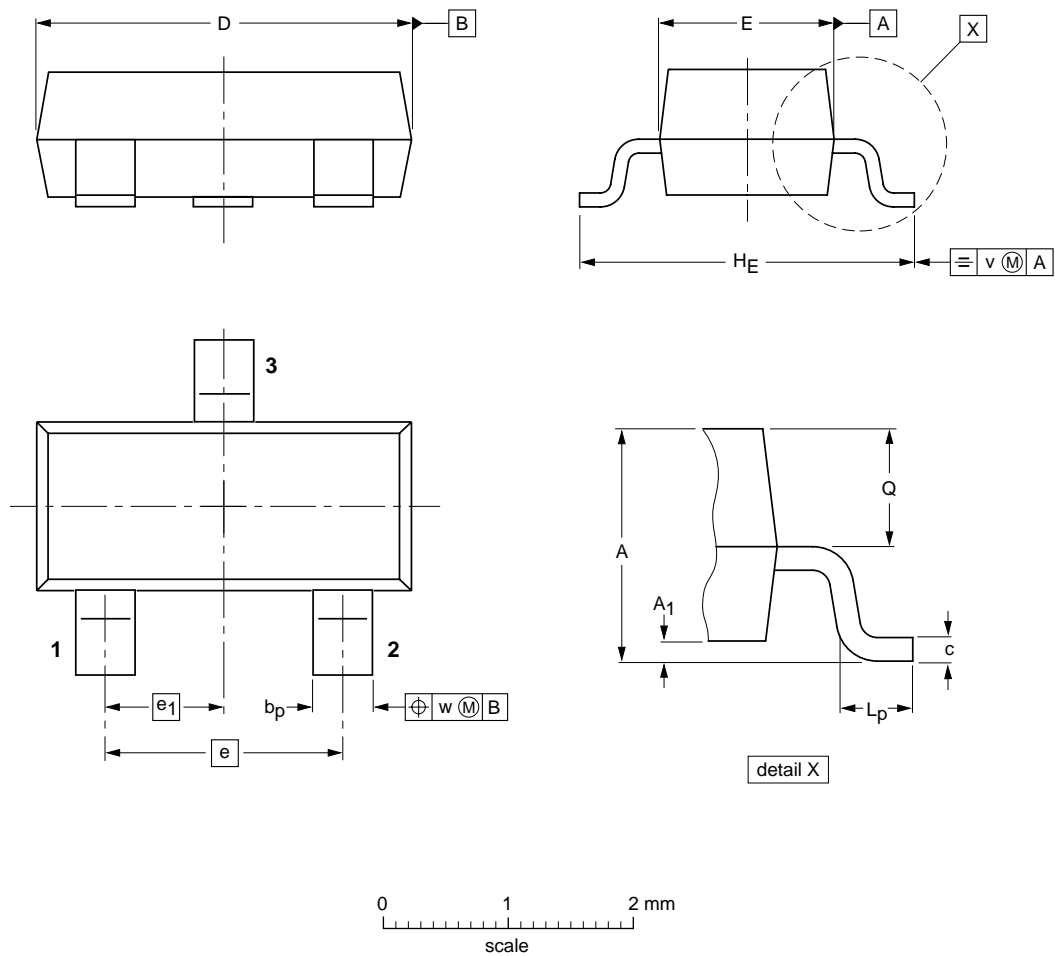


NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 22 kΩ

PDTC124E series


Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

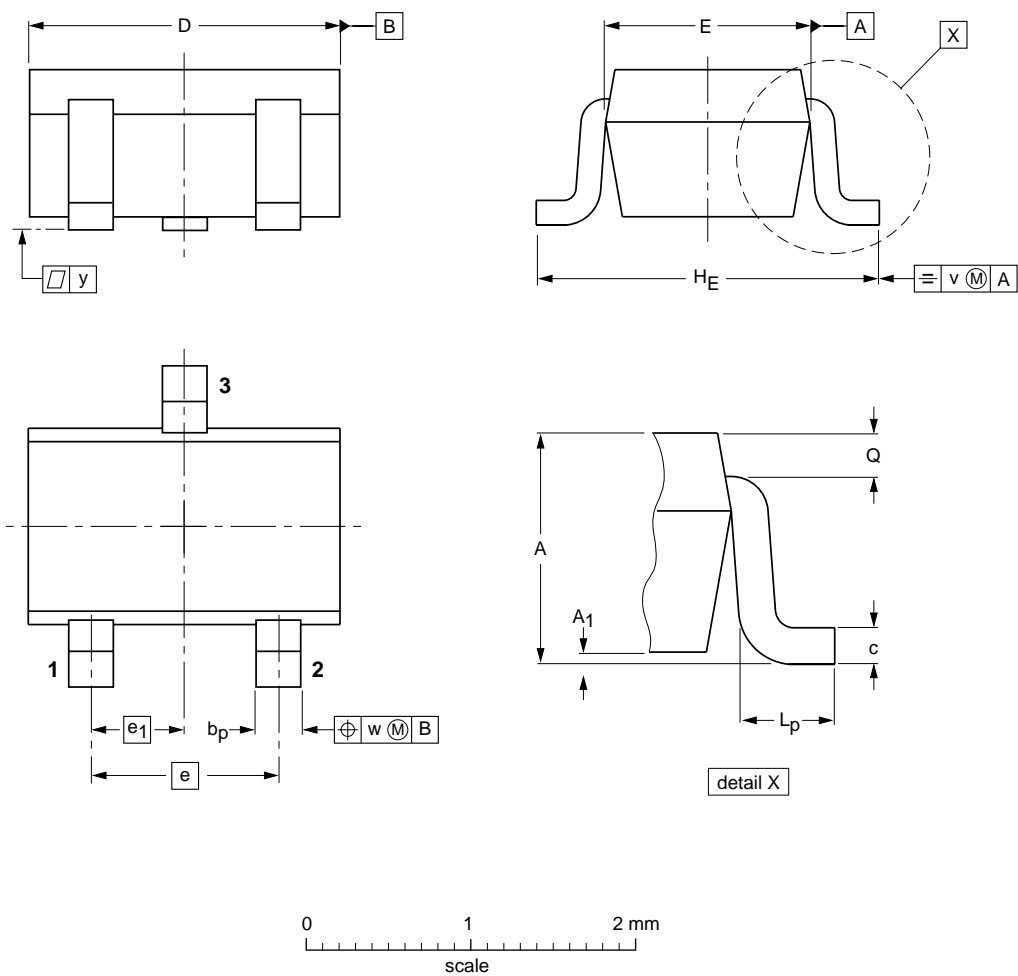
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				<del>97-02-28</del> 99-09-13

NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 22 kΩ

PDTC124E series


Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN resistor-equipped transistors;  
R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

PDTC124E series

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PDTC124E series

#### NOTES

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NPN resistor-equipped transistors;  
R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

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PDTC124E series

#### NOTES

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